

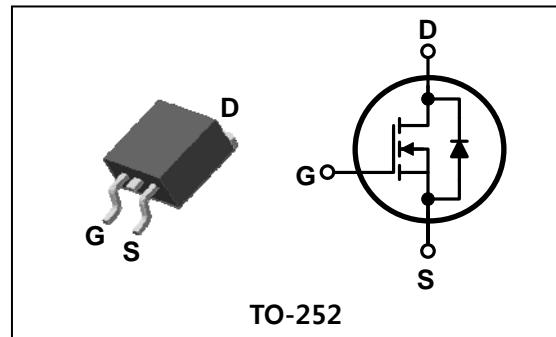
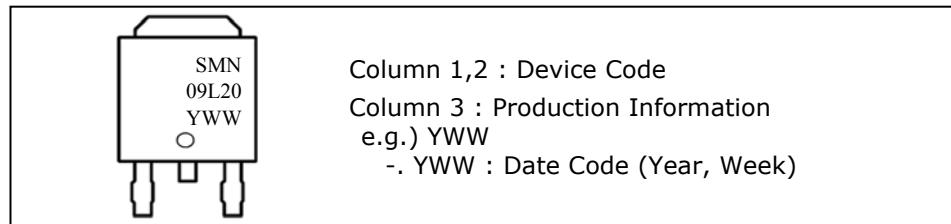
DC-DC CONVERTER APPLICATION  
HIGH VOLTAGE SWITCHING APPLICATIONS

**Features**

- High Voltage :  $BV_{DSS}=200V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=17pF$ (Typ.)
- Low gate charge :  $Q_g=9nC$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=0.4\Omega$ (Max.)

**Ordering Information**

| Type No.  | Marking  | Package Code |
|-----------|----------|--------------|
| SMN09L20D | SMN09L20 | TO-252       |

**PIN Connection**

**Marking Diagram**

**Absolute maximum ratings ( $T_c=25^\circ C$  unless otherwise noted)**

| Characteristic                   | Symbol    | Rating            | Unit       |
|----------------------------------|-----------|-------------------|------------|
| Drain-source voltage             | $V_{DSS}$ | 200               | V          |
| Gate-source voltage              | $V_{GSS}$ | $\pm 30$          | V          |
| Drain current (DC) *             | $I_D$     | $T_c=25^\circ C$  | A          |
|                                  |           | $T_c=100^\circ C$ | A          |
| Drain current (Pulsed) *         | $I_{DM}$  | 36                | A          |
| Power dissipation                | $P_D$     | 45                | W          |
| Avalanche current (Single) ②     | $I_{AS}$  | 9                 | A          |
| Single pulsed avalanche energy ② | $E_{AS}$  | 232               | mJ         |
| Avalanche current (Repetitive) ① | $I_{AR}$  | 9                 | A          |
| Repetitive avalanche energy ①    | $E_{AR}$  | 9.5               | mJ         |
| Junction temperature             | $T_J$     | 150               | $^\circ C$ |
| Storage temperature range        | $T_{stg}$ | -55~150           |            |

\* Limited by maximum junction temperature

| Characteristic     | Symbol              | Typ.          | Max. | Unit         |
|--------------------|---------------------|---------------|------|--------------|
| Thermal resistance | Junction-case       | $R_{th(J-C)}$ | -    | $^\circ C/W$ |
|                    | Junction-ambient ** | $R_{th(J-A)}$ | -    |              |

\*\* When mounted on the minimum pad size recommended (PCB Mount)

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

| <b>Characteristic</b>                       | <b>Symbol</b>            | <b>Test Condition</b>                                     | <b>Min.</b> | <b>Typ.</b> | <b>Max.</b> | <b>Unit</b>   |
|---|--------------------------|---|-------------|-------------|-------------|---------------|
| Drain-source breakdown voltage              | $\text{BV}_{\text{DSS}}$ | $I_D=250\mu\text{A}, V_{GS}=0$                            | 200         | -           | -           | V             |
| Gate threshold voltage                      | $V_{GS(\text{th})}$      | $I_D=250\mu\text{A}, V_{DS}=V_{GS}$                       | 1.0         | -           | 2.25        | V             |
| Drain-source cut-off current                | $I_{\text{DSS}}$         | $V_{DS}=200\text{V}, V_{GS}=0\text{V}$                    | -           | -           | 1           | $\mu\text{A}$ |
| Gate leakage current                        | $I_{\text{GSS}}$         | $V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$                 | -           | -           | $\pm 100$   | nA            |
| Drain-source on-resistance <sup>(4)</sup>   | $R_{DS(\text{ON})}$      | $V_{GS}=10\text{V}, I_D=4.5\text{A}$                      | -           | 0.34        | 0.40        | $\Omega$      |
| Forward transfer conductance <sup>(4)</sup> | $g_{fs}$                 | $V_{DS}=10\text{V}, I_D=4.5\text{A}$                      | -           | 5.5         | -           | S             |
| Input capacitance                           | $C_{iss}$                | $V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$      | -           | 556         | 600         | pF            |
| Output capacitance                          | $C_{oss}$                |   | -           | 100         | 150         |               |
| Reverse transfer capacitance                | $C_{rss}$                |   | -           | 17          | 30          |               |
| Turn-on delay time                          | $t_{d(on)}$              | $V_{DD}=100\text{V}, I_D=9\text{A}$<br>$R_G=25\Omega$     | -           | 18          | -           | ns            |
| Rise time                                   | $t_r$                    |   | -           | 36          | -           |               |
| Turn-off delay time                         | $t_{d(off)}$             |   | -           | 133         | -           |               |
| Fall time                                   | $t_f$                    |   | -           | 45          | -           |               |
| Total gate charge                           | $Q_g$                    | $V_{DS}=160\text{V}, V_{GS}=5\text{V}$<br>$I_D=9\text{A}$ | -           | 9           | 15          | nC            |
| Gate-source charge                          | $Q_{gs}$                 |   | -           | 4           | -           |               |
| Gate-drain charge                           | $Q_{gd}$                 |   | -           | 3           | -           |               |

**Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

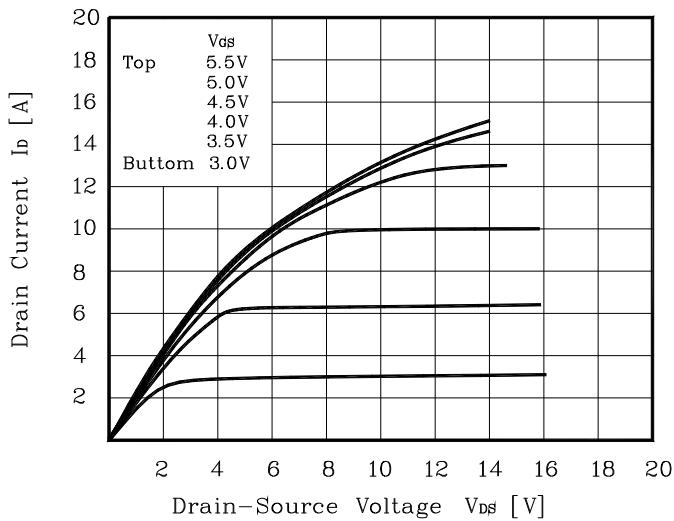
| <b>Characteristic</b>                  | <b>Symbol</b> | <b>Test Condition</b>  | <b>Min.</b> | <b>Typ.</b> | <b>Max.</b> | <b>Unit</b> |
|--|---------------|--|-------------|-------------|-------------|-------------|
| Source current (DC)                    | $I_S$         | Integral reverse diode in the MOSFET                                   | -           | -           | 9           | A           |
| Source current (Pulsed) <sup>(1)</sup> | $I_{SM}$      |  | -           | -           | 36          |             |
| Forward voltage <sup>(4)</sup>         | $V_{SD}$      | $V_{GS}=0\text{V}, I_S=9\text{A}$                                      | -           | -           | 1.5         | V           |
| Reverse recovery time                  | $t_{rr}$      | $I_S=9\text{A}, V_{GS}=0\text{V}$<br>$dI_F/dt=100\text{A}/\mu\text{s}$ | -           | 158         | -           | ns          |
| Reverse recovery charge                | $Q_{rr}$      |  | -           | 0.97        | -           | uC          |

Note :

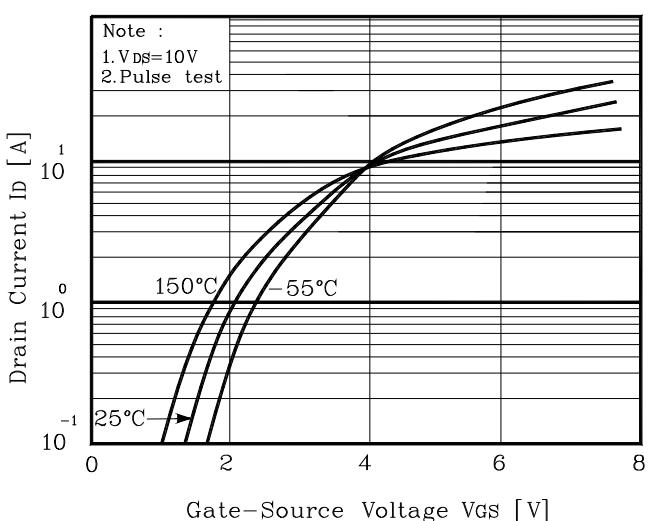
- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ②  $L=4.3\text{mH}, I_{AS}=9\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
- ③ Pulse Test : Pulse width  $\leq 300\text{us}$ , Duty cycle  $\leq 2\%$
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

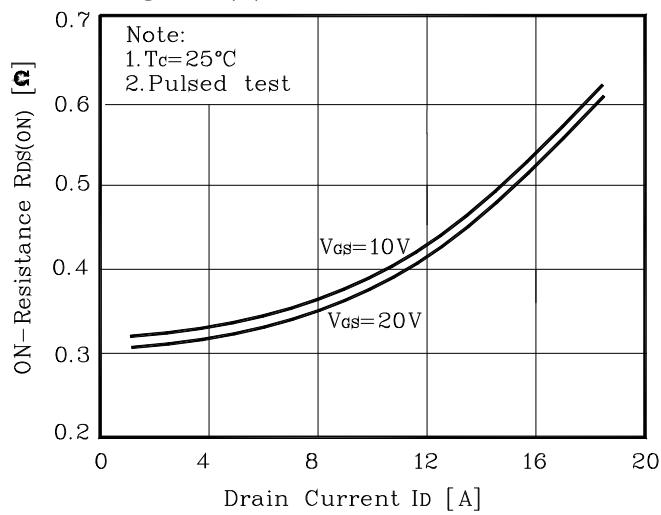
**Fig. 1  $I_D$  -  $V_{DS}$**



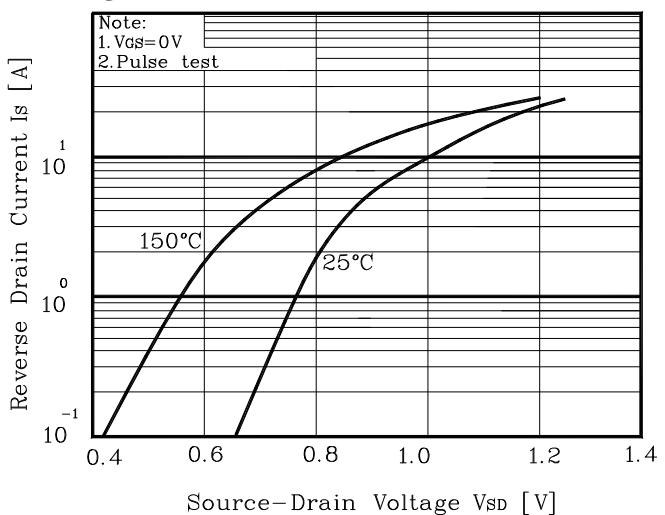
**Fig. 2  $I_D$  -  $V_{GS}$**



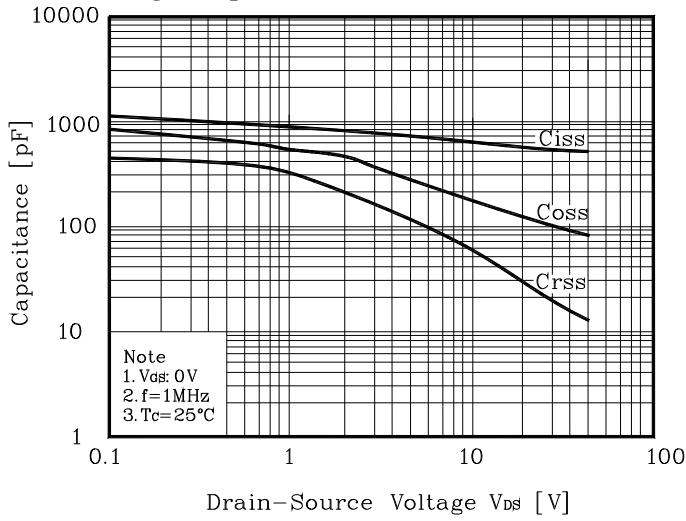
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



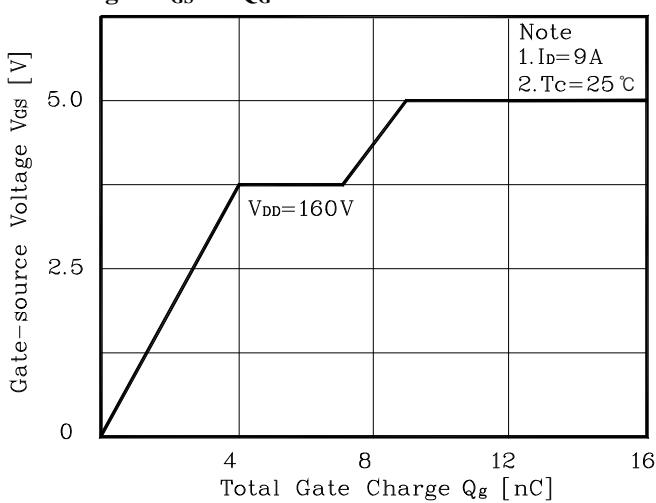
**Fig. 4  $I_S$  -  $V_{SD}$**



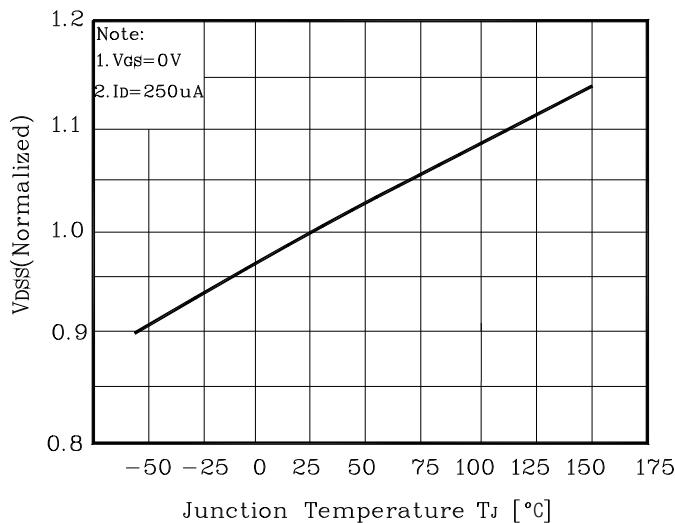
**Fig. 5 Capacitance -  $V_{DS}$**



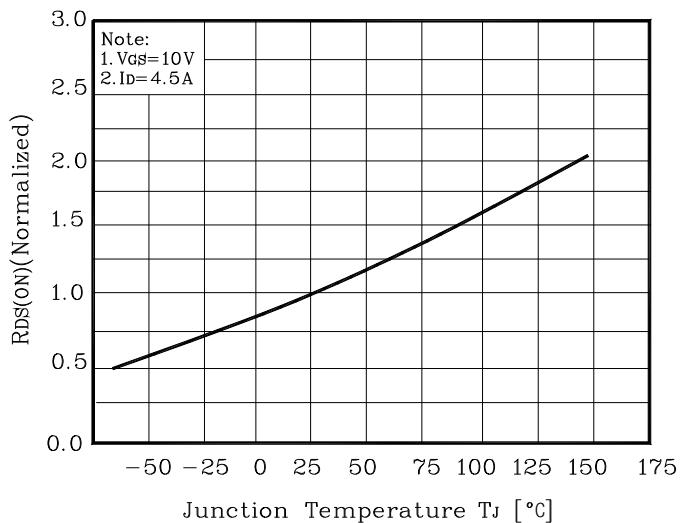
**Fig. 6  $V_{GS}$  -  $Q_G$**



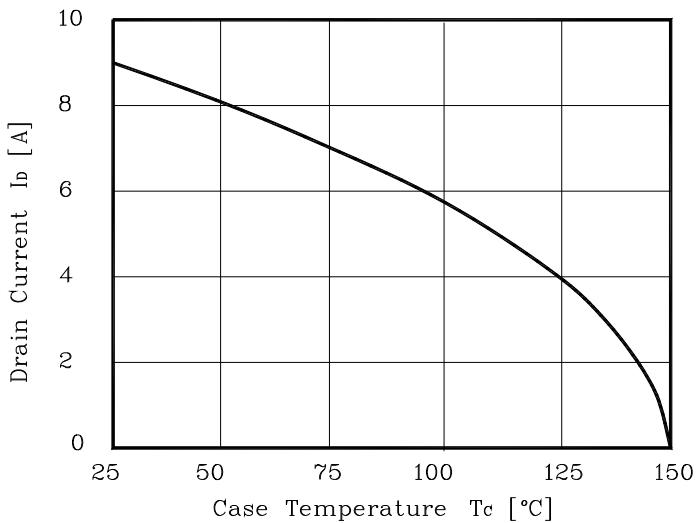
**Fig. 7  $V_{DSS}$  -  $T_J$**



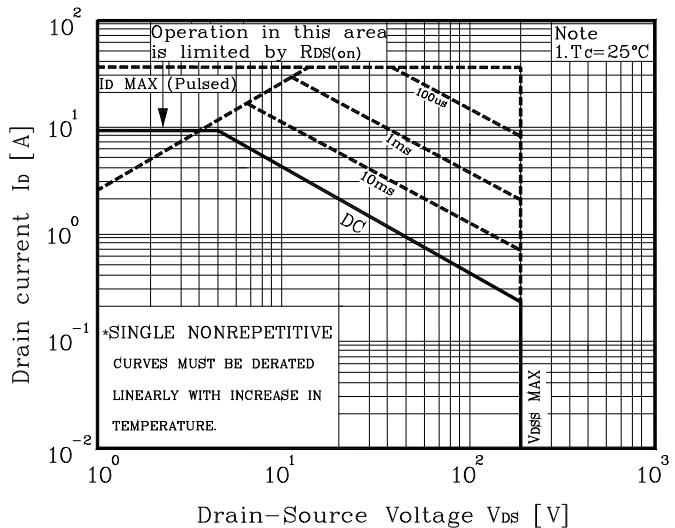
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



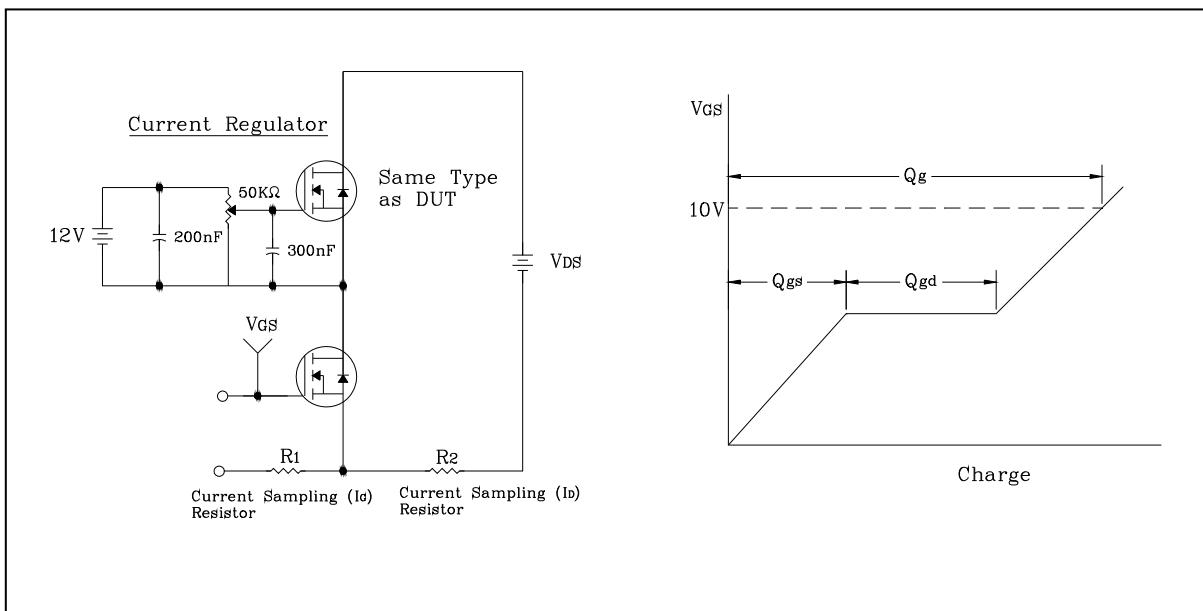
**Fig. 9  $I_D$  -  $T_c$**



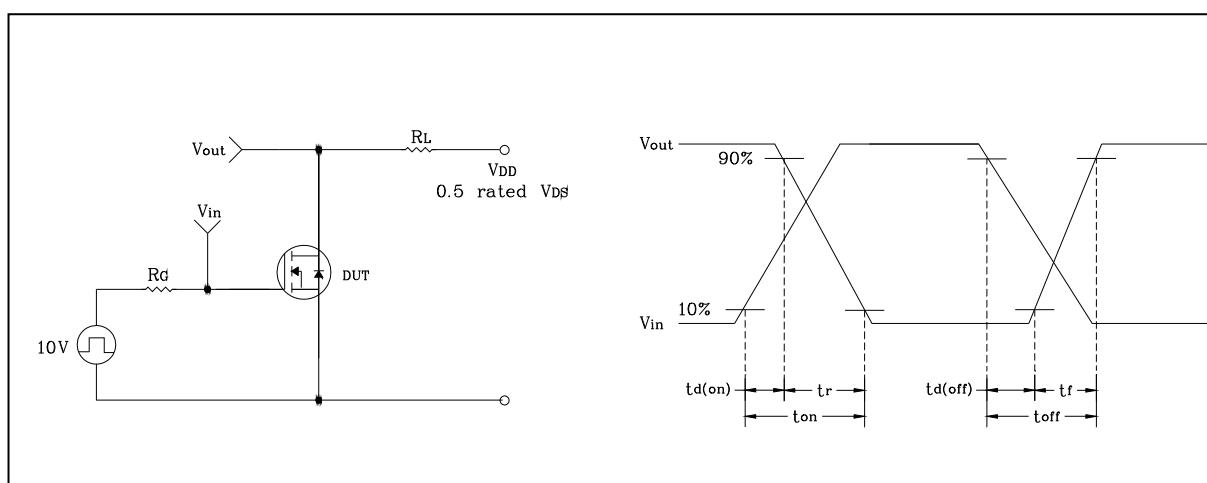
**Fig. 10 Safe Operating Area**



**Fig. 11 Gate Charge Test Circuit & Waveform**



**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

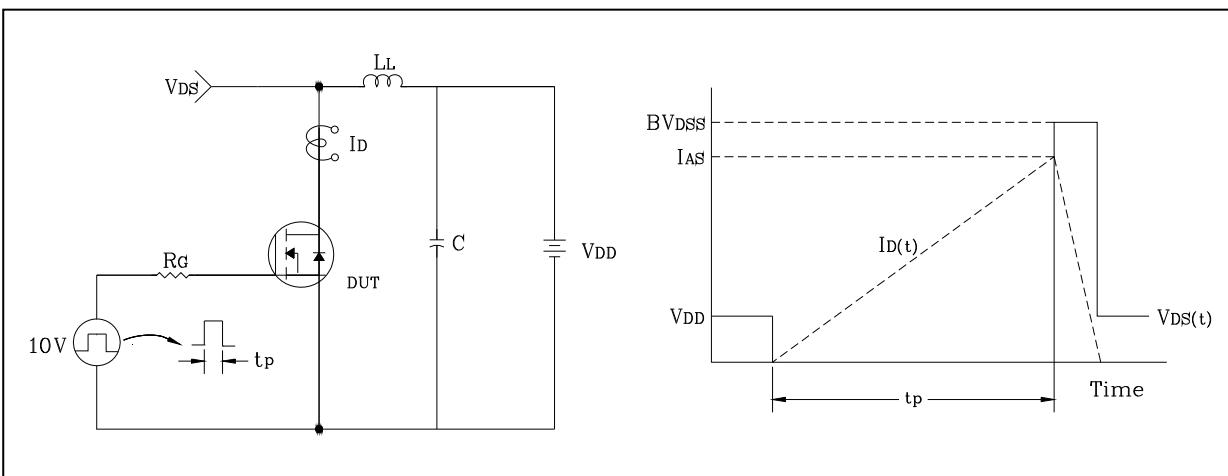
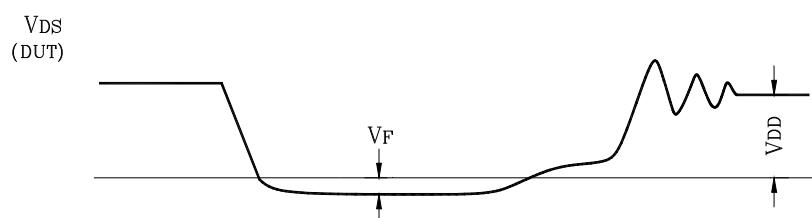
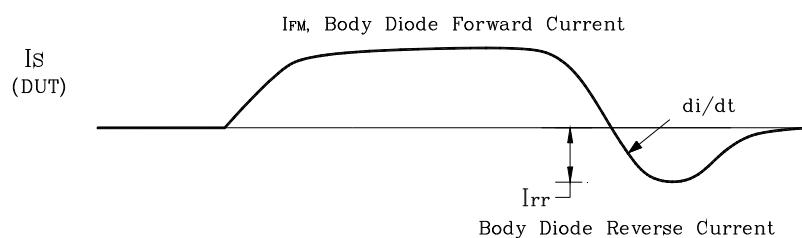
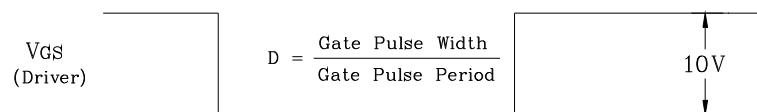
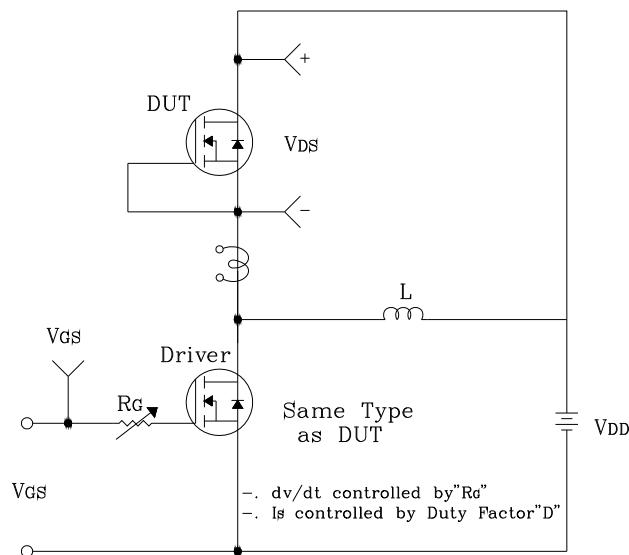
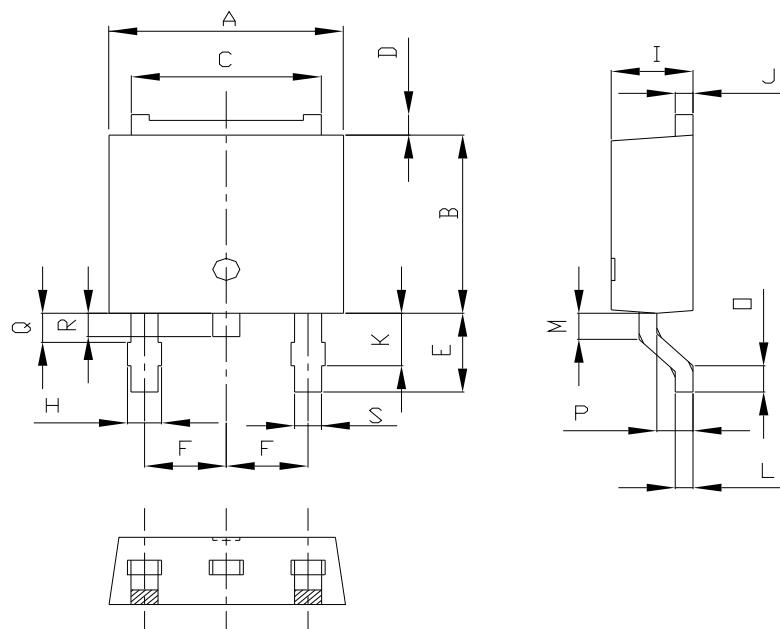


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform

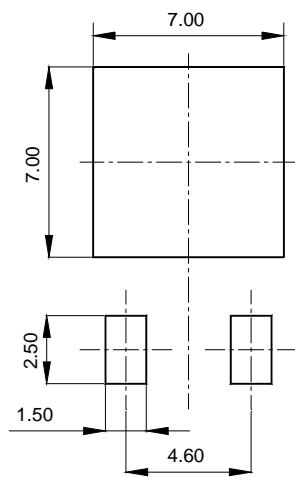


**Outline Dimension**

unit: mm



| SYMBOL | MILLIMETERS |          |         | NOTE |
|--------|-------------|----------|---------|------|
|        | MINIMUM     | NOMINAL  | MAXIMUM |      |
| A      | 6.40        | 6.60     | 6.80    |      |
| B      | 5.90        | 6.10     | 6.30    |      |
| C      | 5.04        | 5.34     | 5.64    |      |
| D      | 0.50        | 0.70     | 0.90    |      |
| E      | 2.50        | 2.70     | 2.90    |      |
| F      | 2.10        | 2.30     | 2.50    |      |
| H      |             | 0.96 MAX |         |      |
| I      | 2.20        | 2.30     | 2.40    |      |
| J      | 0.40        | 0.50     | 0.60    |      |
| K      | 1.60        | 1.80     | 2.00    |      |
| L      | 0.40        | 0.50     | 0.60    |      |
| M      | 0.81        | 0.91     | 1.01    |      |
| O      | 0.80        | 0.90     | 1.00    |      |
| P      | 0.90        | 1.00     | 1.10    |      |
| Q      |             | 0.95 MAX |         |      |
| R      | 0.60        | 0.80     | 1.00    |      |
| S      | 0.66        | 0.76     | 0.86    |      |

**\* Recommended Land Pattern [unit: mm]**

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